

High-Speed Dual SPDT Switch

UM9636 *QFN10 1.8×1.4*

General Description

The UM9636 is a high-speed, low-power dual single-pole/double-throw (SPDT) analog switch that operates from a single +2.7V to +12V supply.

The UM9636 features 720MHz -3dB bandwidth, -67dB crosstalk and -58dB off-isolation at 10MHz frequency. Wide bandwidth and low on-resistance allow it to pass high-speed differential signal with good signal integrity. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. Its high channel-to-channel crosstalk rejection results in minimal noise interference. Key applications for the UM9636 are logic level translation, pulse generator, and high speed or low noise signal switching in precision instrumentations and portable device designs.

The switch is available in Pb-free QFN10 1.8×1.4 package.

Applications

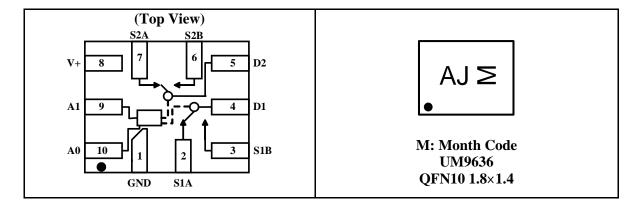
- High-End Data Acquisition
- Medical Instruments
- Precision Instruments
- High Speed Communications Applications
- Automated Test Equipment
- Sample and Hold Applications

Features

- Ron is Typically 83Ω at $V_{CC}=12V$
- Channel On-Capacitance: 6.5pF (Typical)
- Typically 720MHz -3dB Bandwidth (or Data Frequency)
- Low Crosstalk: Typically -67dB (10MHz)
- Low Off-Isolation: Typically -58dB (10MHz)
- Low Voltage, 1.65 V CMOS/TTL Compatible
- Low Current Consumption: 1µA
- V_{CC} Operating Range: +2.7V to +12V
- Lead(Pb)-Free QFN10 Package

Pin Configurations

Top View



Ordering Information

Part Number	Packaging Type	Marking Code	Shipping Qty	
UM9636	QFN10 1.8×1.4	AJ	3000pcs/7 Inch Tape & Reel	



Truth Table

Select	On Switches	
A1	A0	UM9636
X	0	D1 to S1A
X	1	D1 to S1B
0	X	D2 to S2A
1	X	D2 to S2B

Pin Description

Pin	Name	Function
1	GND	Ground Connection
2	S1A	Data Ports
3	S1B	Data Ports
4	D1	Data Ports
5	D2	Data Ports
6	S2B	Data Ports
7	S2A	Data Ports
8	V+	Positive Supply Voltage
9	A1	Select Input
10	A0	Select Input

Absolute Maximum Ratings

Symbol	Parameter	Limit	Unit	
V+	Supply Voltage	-0.5 to +14V		
V_{IS}	Analog Switch Input Voltage	-0.5 to (V _{CC} +0.3)	V	
V_{IN}	Digital Select Input Voltage	-0.5 to $(V_{CC}+0.3)$		
I_D	Continuous DC Current	50		
P_{P}	Peak Current, S or D (Pulsed 1 ms, 10 % Duty Cycle)	100	mA	
P_D	Power Dissipation	0.28	W	
T_{O}	Operating Temperature Range	-40 to +85	$^{\circ}$	
T_{STG}	Storage Temperature Range	-65 to +150	C	
	HBM			
ESD	I/O to GND	4000	V	
	All Pins	2000		



Electrical Characteristics

					Limits (-40°C to 85°C)			
Symbol	Parameter	Test Conditions	V+ (V)	Temp	Min	Typ (Note 1)	Max	Unit
DC Electrica	al Characteristics							
V _{ANALOG}	Analog Signal Range			Full			12	V
I_{CC}	Quiescent Supply Current	V _{IN} =0V, or V+	12	Room Full		0.01	0.5 1	μА
I_{GND}	Ground Current	V _{IN} -UV, OI V+	12	Room Full	-0.5 -1	-0.01		μΑ
I_{IH}	Input Leakage Current, V _{IN} High	$V_{AX}=1.65V$	12	Full	-0.1	0.01	0.1	μА
$I_{\rm IL}$	Input Leakage Current, V _{IN} Low	$V_{AX}\!\!=\!\!0.5V$	12	Full	-0.1	0.01	0.1	μΑ
$I_{D(on)}$	Channel On Leakage Current	$V+=12V, V_D=V_S 11V/1V$	12	Room Full	-1.0	±0.01	1.0 2.0	μА
$I_{D(\mathrm{off})}$	OFF State Leakage Current	V+=12V, V _D =1V/11V,	12	Room Full	-11.0	±0.01	11.0 15.0	μΑ
$I_{S(\mathrm{off})}$	(Note 2)	$V_{\rm S}=11V/1V$	12	Room Full	-11.0	±0.01	11.0 15.0	μΑ
V_{IH}	Input High Voltage		12	Full	1.65			V
$V_{\rm IL}$	Input Low Voltage		12	Full			0.5	V
R_{ON}	On-Resistance (Note 3)	$V_D=11.3V$ $I_S=1mA$	12	Room Full		83	110 125	Ω
$\Delta R_{\rm ON}$	On Resistance Match Between Channels (Note 3, 4, 5)	$V_D=11.3V$ $I_S=1mA$	12	Room Full		2	4 6	Ω
R_{FLAT}	On Resistance Flatness (Note 3, 4, 6)	V_D =0.7, 6.5, 11.3V I_S =1mA	12	Room Full		33	45 50	Ω
AC Electrica	al Characteristics							
$t_{\rm ON}$	Turn On Time	R_L =300 Ω , C_L =35pF	12	Room Full		30	70 80	ns
t_{OFF}	Turn Off Time	R_L =300 Ω , C_L =35pF	12	Room Full		15	55 65	ns
t_{BBM}	Break Before Make Time (Note 7)	$R_L=300\Omega$, $C_L=35pF$	12	Room Full	5 2	15		ns
THD	Total Harmonic Distortion	$\begin{array}{c} \text{Signal=1V}_{\text{RMS}},\\ 20\text{Hz to }20\text{kHz},\\ R_{\text{L}}{=}600\Omega \end{array}$	12	Room		0.01		%
Charge Injection	Q _{INJ}	$C_L=1nF, R_{GEN}=0\Omega, \ V_{GEN}=0V$	12	Room		23.5		pC
O_{IRR}	Off Isolation (Note 8)	R_L =50 Ω , C_L =5pF, f=10MHz	12	Room		-58		dB
X_{TALK}	Crosstalk	R_L =50 Ω , C_L =5pF, f=10MHz	12	Room		-67		dB
BW	-3dB Bandwidth	$R_L=50\Omega$	12	Room		720		MHz
Capacitance								
C_{IN}	Control Pin Input Capacitance	f=1MHz		Room		3		pF
C_{OFF}	Switch Off Capacitance	f=1MHz	12	Room		2.0		pF
C_{ON}	Switch On Capacitance	f=1MHz	12	Room		7.7		pF

Note 1: Typically values are at $T_A=+25$ °C.

Note 2: The high OFF State Leakage Current is because of pull down resistor

Note 3: Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

Note 4: Parameter is characterized but not tested in production.

Note 5: $\Delta R_{ON} = \mid R_{ON \, (S1A/S1B)} - R_{ON(S2A/S2B)} \mid$ measured at identical V_{CC} , temperature and voltage levels.

Note 6: Flatness is defined as the difference between the maximum and minimum value of On Resistance over the specified range of conditions.

Note 7: Guaranteed by design. Note 8: Off Isolation=20log10 [V_D/V_{SA/SB}].



Electrical Characteristics

	Po control				Limi	its (–40°C to 8	85°C)	Unit
Symbol	Parameter	Test Conditions	V+ (V)	Тетр	Min	Typ (Note 1)	Max	
DC Electrica	l Characteristics							
V_{ANALOG}	Analog Signal Range			Full			5	V
I_{CC}	Quiescent Supply Current	$V_{IN}=0V$, or $V+$	5	Room Full		0.01	0.5 1	μА
I_{GND}	Ground Current	VIN-OV, OF VI	J	Room Full	-0.5 -1	-0.01		- μΑ
I_{IH}	Input Leakage Current, V _{IN} High	$V_{AX}=1.4V$	5	Full	-0.1	0.01	0.1	μΑ
${ m I}_{ m IL}$	Input Leakage Current, V _{IN} Low	$V_{AX}=0.5V$	5	Full	-0.1	0.01	0.1	μΑ
$I_{D(on)}$	Channel On Leakage Current	$V_{+}=5.5V, V_{D}=V_{S} 4.5V/1V$	5.5	Room Full	-1.0	±0.01	1.0 2.0	μΑ
$I_{\text{D(off)}}$	OFF State Leakage	V+=5.5V,	5.5	Room Full	-3.0	±0.01	3.0 5.0	μΑ
$I_{S(\mathrm{off})}$	Current (Note 2)	$V_D=1V/4.5V, V_S=4.5V/1V$	5.5	Room Full	-3.0	±0.01	3.0 5.0	μΑ
V_{IH}	Input High Voltage		5	Full	1.4			V
$V_{\rm IL}$	Input Low Voltage		5	Full			0.5	V
R_{ON}	On-Resistance (Note 3)	$V_D=4V$ $I_S=1mA$	5	Room Full		300	350 400	Ω
ΔR_{ON}	On Resistance Match Between Channels (Note 3, 4, 5)	$V_D=4V$ $I_S=1mA$	5	Room Full		6	12 15	Ω
AC Electrica	l Characteristics							
t_{ON}	Turn On Time	$R_L = 300\Omega, C_L = 35pF$	5	Room Full		55		ns
t_{OFF}	Turn Off Time	$R_L=300\Omega$, $C_L=35pF$	5	Room Full		30		ns
$t_{ m BBM}$	Break Before Make Time (Note 6)	R_L =300 Ω , C_L =35pF	5	Room Full		36		ns
THD	Total Harmonic Distortion	Signal= $1V_{RMS}$, 20Hz to 20kHz, R_L = 600Ω	5	Room		2.2		%
Charge Injection	Q _{INJ}	$\begin{array}{c} C_L \!\!=\! 1 n F, R_{GEN} \!\!=\!\! 0 \Omega, \\ V_{GEN} \!\!=\!\! 0 V \end{array}$	5	Room		10		pC
O_{IRR}	Off Isolation (Note 7)	R_L =50 Ω , C_L =5 pF , f =10 MHz	5	Room		-58		dB
X_{TALK}	Crosstalk	R_L =50 Ω , C_L =5pF, f=10MHz	5	Room		-68		dB
BW	-3dB Bandwidth	$R_L = 50\Omega$	5	Room		610		MHz
Capacitance								
C_{IN}	Control Pin Input Capacitance	f=1MHz		Room		3		pF
C_{OFF}	Switch Off Capacitance	f=1MHz	5	Room		2.1		pF
C_{ON}	Switch On Capacitance	f=1MHz	5	Room		8.1		pF
			_				_	_

Note 1: Typically values are at T_A=+25 °C.

Note 2: The high OFF State Leakage Current is because of pull down resistor

Note 3: Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

Note 4: Parameter is characterized but not tested in production.

Note 5: $\Delta R_{ON} = \mid R_{ON \, (S1A/S1B)} - R_{ON(S2A/S2B)} \mid$ measured at identical V_{CC} , temperature and voltage levels.

Note 6: Guaranteed by design. Note 7: Off Isolation=20log10 [V_D/V_{SA/SB}].



Electrical Characteristics

				Temp	Limi	ts (-40°C to 8	85°C)	
Symbol	Parameter	Test Conditions	V+ (V)		Min	Typ (Note 1)	Max	Unit
DC Electrica	l Characteristics							
V_{ANALOG}	Analog Signal Range			Full			3	V
I_{CC}	Quiescent Supply Current	V _{IN} =0V, or V+	3	Room Full		0.01	0.5 1	μА
I_{GND}	Ground Current	VIN-OV, OI VI	3	Room Full	-0.5 -1	-0.01		μΑ
${ m I}_{ m IH}$	Input Leakage Current, V _{IN} High	$V_{AX}=1.4V$	3	Full	-0.1	0.01	0.1	μΑ
$I_{\rm IL}$	Input Leakage Current, V _{IN} Low	$V_{AX} = 0.5V$	3	Full	-0.1	0.01	0.1	μА
$I_{\mathrm{D}(\mathrm{on})}$	Channel On Leakage Current	$V+=3.3V, V_D=V_S 3V/1V$	3.3	Room Full	-1.0	±0.01	1.0 2.0	μΑ
$I_{D(\mathrm{off})}$	OFF State Leakage	V+=3.3V, V _D =1V/3V,	3.3	Room Full	-1.0	±0.01	1.0 2.0	μΑ
$I_{S(\mathrm{off})}$	Current	$V_{S}=1 V/3 V,$ $V_{S}=3 V/1 V$	3.3	Room Full	-1.0	±0.01	1.0 2.0	μА
V_{IH}	Input High Voltage		3	Full	1.4			V
$V_{\rm IL}$	Input Low Voltage		3	Full			0.5	V
R_{ON}	On-Resistance (Note 2)	$V_D=1.5V$ $I_S=1mA$	3	Room Full		500	550 650	Ω
$\Delta R_{\rm ON}$	On Resistance Match Between Channels (Note 2, 3, 4)	$V_D=1.5V$ $I_S=1mA$	3	Room Full		10	14 18	Ω
AC Electrica	l Characteristics							
t _{ON}	Turn On Time	R_L =300 Ω , C_L =35pF	3	Room Full		96		ns
t_{OFF}	Turn Off Time	R_L =300 Ω , C_L =35pF	3	Room Full		60		ns
$t_{ m BBM}$	Break Before Make Time (Note 5)	$\begin{array}{c} R_L{=}300\Omega, \\ C_L{=}35pF \end{array}$	3	Room Full		77		ns
THD	Total Harmonic Distortion	Signal= $1V_{RMS}$, 20Hz to 20kHz, R_L = 600Ω	3	Room		2.2		%
Charge Injection	Q _{INJ}	$C_L=1$ nF, $R_{GEN}=0$ Ω, $V_{GEN}=0$ V	3	Room		6.6		pC
O_{IRR}	Off Isolation (Note 6)	R_L =50 Ω , C_L =5 pF , f =10 MHz	3	Room		-57		dB
X_{TALK}	Crosstalk	R_L =50 Ω , C_L =5pF, f=10MHz	3	Room		-69		dB
BW	-3dB Bandwidth	$R_L=50\Omega$	3	Room		525		MHz
Capacitance								
C_{IN}	Control Pin Input Capacitance	f=1MHz		Room		3.1		pF
C_{OFF}	Switch Off Capacitance	f=1MHz	3	Room		2.1		pF
C_{ON}	Switch On Capacitance	f=1MHz	3	Room		8.3		pF

Note 1: Typically values are at T_A =+25 °C. Note 2: Guaranteed by design. Resistance measurements do not include test circuit or package resistance. Note 3: Parameter is characterized but not tested in production.

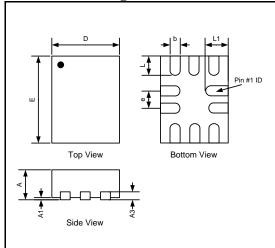
Note 4: $\Delta R_{ON} = |R_{ON}_{(S1A/S1B)} - R_{ON(S2A/S2B)}|$ measured at identical V_{CC} , temperature and voltage levels. Note 5: Guaranteed by design. Note 6: Off Isolation=20log10 $[V_D/V_{SA/SB}]$.



Package Information

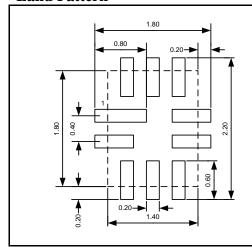
UM9636: QFN10 1.80×1.40

Outline Drawing



DIMENSIONS								
Symbol	MILLIMETERS			INCHES				
Symbol	Min	Тур	Max	Min	Тур	Max		
A	0.50	0.55	0.60	0.020	0.022	0.024		
A1	A1 0.00		0.05	0.000	1	0.002		
A3	0.15REF			0.006REF				
b	0.15	0.20	0.25	0.006	0.008	0.010		
D	1.35	1.40	1.45	0.053	0.055	0.057		
Е	1.75	1.80	1.85	0.069	0.071	0.073		
e	0.40BSC			0.016BSC				
L	0.30 0.40		0.50	0.012	0.016	0.020		
L1	0.40	0.50	0.60	0.016	0.020	0.024		

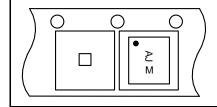
Land Pattern



NOTES:

- 1. Compound dimension: 1.80×1.40;
- 2. Unit: mm
- 3. General tolerance ± 0.05 mm unless otherwise specified;
- 4. The layout is just for reference.

Tape and Reel Orientation





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Union Semiconductor, Inc

Add: Unit 606, No.570 Shengxia Road, Shanghai 201210

Tel: 021-51093966 Fax: 021-51026018

Website: www.union-ic.com